



## 650V/ 8A Silicon Carbide Power Schottky Barrier Diode

### Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

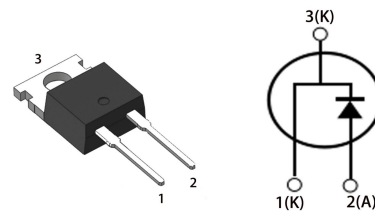
### Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

### Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

Key Characteristics		
$V_{RRM}$	<b>650</b>	<b>V</b>
$I_F, T_c \leq 153^\circ\text{C}$	<b>8</b>	<b>A</b>
$Q_c$	<b>21</b>	<b>nC</b>



Part No.	Package Type	Marking
G4S06508AT	TO-220AC	G4S06508AT

**Maximum Ratings**

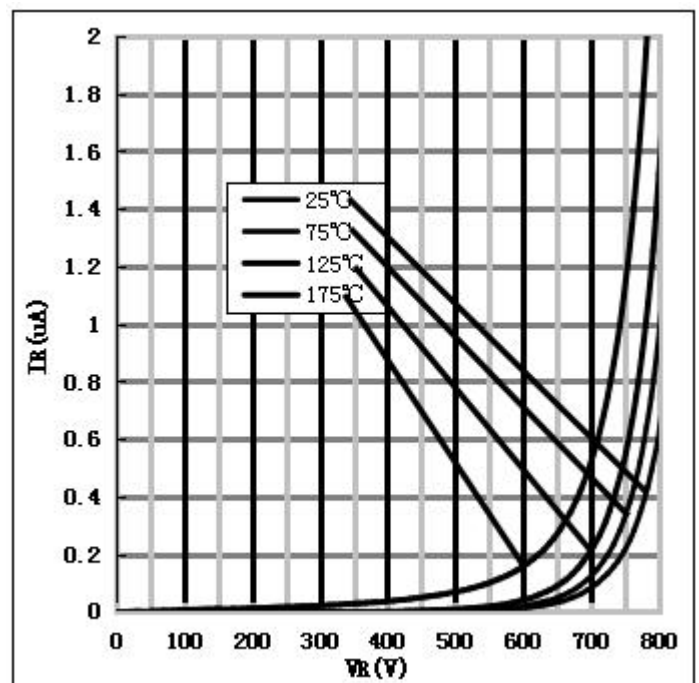
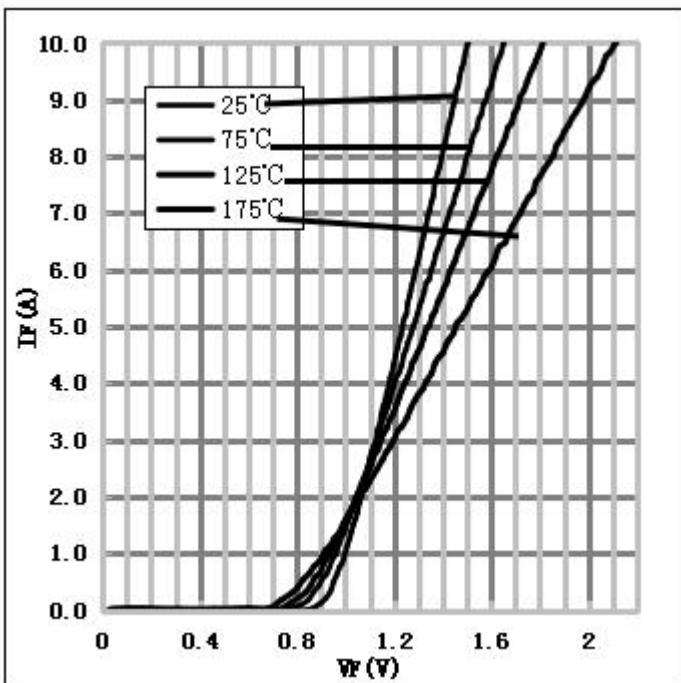
Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$		650	V
Surge Peak Reverse Voltage	$V_{RSM}$		650	V
DC Blocking Voltage	$V_{DC}$		650	V
Continuous Forward Current	$I_F$	$T_C=25^{\circ}C$ $T_C=125^{\circ}C$ $T_C=153^{\circ}C$	24.5 13.2 8	A
Repetitive Peak Forward Surge Current	$I_{FRM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave, $D=0.3$	30	A
Non-repetitive Peak Forward Surge Current	$I_{FSM}$	$T_C=25^{\circ}C$ , $t_p=10ms$ , Half Sine Wave	90	A
Power Dissipation	$P_{TOT}$	$T_C=25^{\circ}C$	99	W
		$T_C=110^{\circ}C$	43	W
Operating Junction	$T_j$		-55°C to 175°C	°C
Storage Temperature	$T_{stg}$		-55°C to 175°C	°C
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in

**Thermal Characteristics**

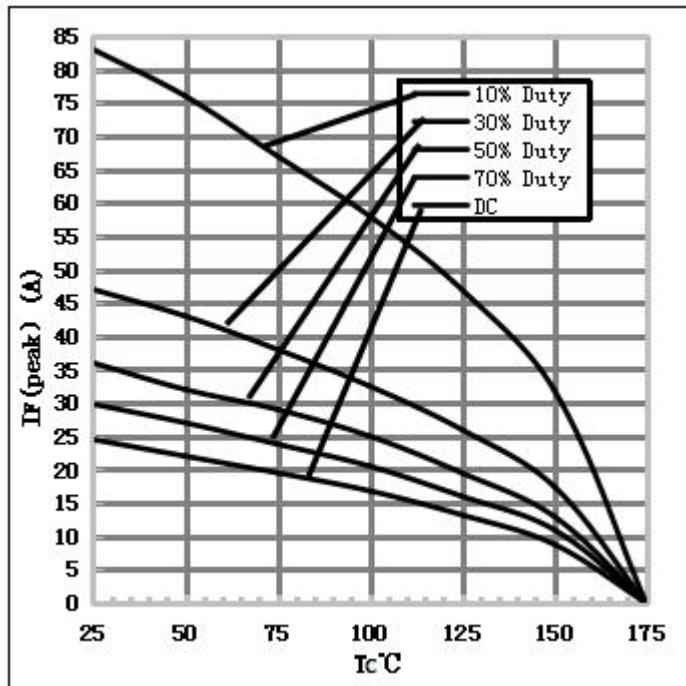
Parameter	Symbol	Test Condition	Value	Unit
			Typ.	
Thermal resistance from junction to case	$R_{thJC}$		1.51	°C/W

Electrical Characteristics

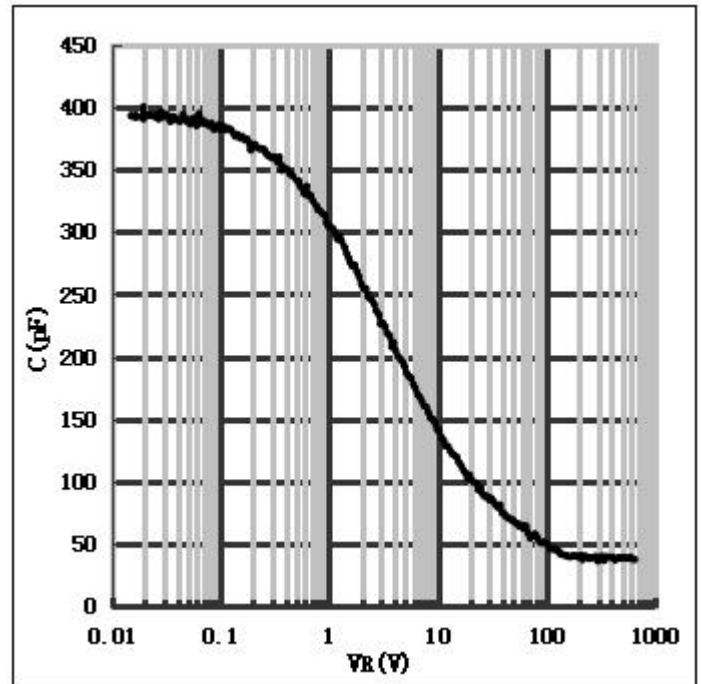
Parameter	Symbol	Test Conditions	Numerical		Unit
			Typ.	Max.	
Forward Voltage	$V_F$	$I_F=8A, T_j=25^\circ C$	1.4	1.7	V
		$I_F=8A, T_j=175^\circ C$	1.85	2.5	
Reverse Current	$I_R$	$V_R=650V, T_j=25^\circ C$	0.2	50	$\mu A$
		$V_R=650V, T_j=175^\circ C$	2.5	100	
Total Capacitive Charge	$Q_C$	$V_R=400V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$	21	-	nC
Total Capacitance	C	$V_R=0V, T_j=25^\circ C, f=1MHz$	395	400	pF
		$V_R=200V, T_j=25^\circ C, f=1MHz$	38	42	
		$V_R=400V, T_j=25^\circ C, f=1MHz$	36	40	

Performance Graphs1) Forward IV characteristics as a function of  $T_j$  :2) Reverse IV characteristics as a function of  $T_j$  :

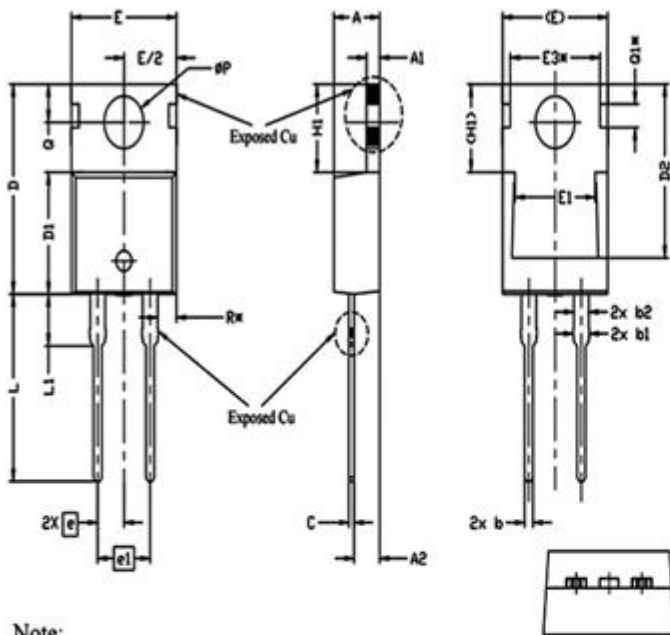
3) Current Derating:



4) Capacitance vs. reverse voltage:



Package TO-220AC



Note:

1. Package Reference: JEDEC TO220, Variation AB.
2. All Dimensions Are In mm.
3. Slot Required, Notch May Be Rounded
4. Dimension D & E Do Not Include Mold Flash. Mold Flash Shall Not Exceed 0.127mm Pre Side. These Dimensions Are Measured At The Outermost Extreme Of The Plastic Body.
5. Thermal Pad Contour Optional Within Dimensions E, H1, D2 & E1.
6. Dimension E2 & H1 Define A Zone Where Stamping And Singulation Irregularities Are Allowed.
7. "\*" is reference .

单位: mm

SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.24	4.44	4.64	
A1	1.15	1.27	1.40	
A2	2.30	2.48	2.70	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
c	0.40	0.50	0.60	
D	14.70	15.37	16.00	4
D1	8.82	8.92	9.02	
D2	12.63	12.73	12.83	5
E	9.96	10.16	10.36	4,5
E1	6.86	7.77	8.89	5
E3*	8.70REF.			
e	254BSC			
e1	508BSC			
H1	6.30	6.45	6.60	5,6
L	13.47	13.72	13.97	
L1	3.60	3.80	4.00	
∅P	3.75	3.84	3.93	
Q	2.60	2.80	3.00	
Q1*	1.73REF.			
R*	1.82REF.			

**Note:** The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: <http://globalpowertech.cn/English/index.asp>

**More product datasheets and company information can be found in:**

<http://globalpowertech.cn/English/index.asp>

